

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("6653157").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/25 09:51
S1	89	("20020009274" "20020158263" "20040061126" "20040195572" "3348056" "3976877" "4058821" "4612083" "4766471" "4811210" "4830444" "4843587" "4851695" "4888625" "4894699" "4988891" "5008554" "5095380" "5249245" "5262980" "5266794" "5268679" "5291324" "5297232" "5339090" "5353247" "5357122" "5362961" "5383042" "5410502" "5478658" "5491571" "5523704" "5546209" "5583570" "5654559" "5738731" "5832147" "5848214" "6111902" "6160828" "6627953" "6661940").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 11:03
S2	2	"US 20040061126"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2006/08/15 09:13
S3	17	((("4888625") or ("3348056") or ("3976877") or ("4058821") or ("4851695") or ("4612083") or ("5249245")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/15 11:59

S4	91	349/17.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:04
S5	241	257/113.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:05
S6	3	S5 and liquid adj crystal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:07
S7	2	S6 and (TFT thin adj film adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:06
S8	1	S7 and (IC integrated adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:05
S9	1	S8 and(amorphous silicon photodiode phototransistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:06
S10	483059	(liquid adj crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:07
S11	57770	S10 and (TFT thin adj film adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:07

S12	12526	S11 and (integrated adj circuit IC)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:44
S13	10	S12 and (amorphous near2 silicon near2 photodiode phototransistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:37
S14	8340	S12 and (amorphous silicon photodiode phototransistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:08
S15	124	S12 and (amorphous silicon) same (photodiode phototransistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:52
S16	37	S15 and cathode same anode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:09
S17	4478	385/14.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:38
S18	175	385/14.ccls. and liquid adj crystal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:38

S19	26	((("5262980") or ("5353247") or ("5410502") or ("5339090") or ("5095380") or ("4830444") or ("5291324") or ("5523704") or ("4811210") or ("4843587") or ("6661940") or ("5832147") or ("5008554")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/15 12:59
S20	2	("5268679").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/15 12:59
S22	21	(US-20060141645-\$ or US-20050168491-\$ or US-20050045881-\$ or US-20050041002-\$ or US-20050030264-\$ or US-20040252867-\$ or US-20040113548-\$ or US-20040043676-\$ or US-20030146439-\$ or US-20040042707-\$ or US-20020057055-\$ or US-20050161754-\$ or US-20040056180-\$). did. or (US-5410502-\$ or US-5268679-\$ or US-4830444-\$ or US-4766471-\$ or US-4612083-\$ or US-6933529-\$ or US-6300612-\$).did. or (JP-2004247405-\$).did.	US-PGPUB; USPAT; DERWENT	OR	ON	2006/08/15 15:00
S23	13	S22 and cathode and anode and amorphous and (tft thin adj film adj transistor)	US-PGPUB; USPAT; DERWENT	OR	ON	2006/08/15 15:06
S24	5	S22 and cathode and anode and amorphous and (tft thin adj film adj transistor) and (semiconductor) and (gate adj electrode) and (gate adj insulat \$5)	US-PGPUB; USPAT; DERWENT	OR	ON	2006/08/15 15:27

S25	1	cathode same anode same amorphous same (tft thin adj film adj transistor) same (semiconductor) same (gate adj electrode) same (gate adj insulat \$5)	US-PGPUB; USPAT; DERWENT	OR	ON	2006/08/15 15:42
S26	145	cathode same anode same amorphous same (tft thin adj film adj transistor)	US-PGPUB; USPAT; DERWENT	OR	ON	2006/08/15 15:43
S27	9	"US 6664732"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2006/08/15 16:00
S28	588	349/74.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/24 16:35
S29	87	349/74.ccls. and (photodiode diode sensor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/24 16:35
S30	319	349/24,25.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/24 16:42
S31	806	349/24,28.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/24 16:42
S32	6683	"349"/\$.ccls. and (photo near2 diode photodiode diode sensor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/24 16:43
S33	31130	(liquid adj crystal).clm.	USPAT	OR	ON	2008/01/24 16:44
S34	187298	(sensor photodiode photo near2 diode). clm.	USPAT	OR	ON	2008/01/24 16:44

S35	128179	(electronic adj circuit tft transistor).clm.	USPAT	OR	ON	2008/01/24 16:45
S36	209	S33 and S34 and S35	USPAT	OR	ON	2008/01/24 16:45

1/ 25/ 2008 10:42:12 AM

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